## **AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

## **LISTING OF CLAIMS:**

- 1. (Currently Amended) A metal laminate comprising which includes a layer obtained by laminating a metal layer laminated to and an insulating layer, where the insulating layer is subjected to an etching processing, wherein, in a surface of the metal layer which is positioned at such a side that the metal layer comes in contact with the insulating layer, respective concentrations of main metal element and oxygen element constituting the metal layer are measured from the surface of the metal layer towards the inside of the metal layer in a time-elapsing manner according to AES (Auger electron spectroscopy) and a value of the thickness of a metal oxide film of the surface of the metal layer measured at a time when atomic concentrations of the main metal element and the oxygen element constituting the metal layer are become equal to each other is in a range of at least 0Å to less than 50Å.
- 2. (Original) The metal laminate according to claim 1, wherein the metal layer includes at least one element selected from the group consisting of iron element, copper element, aluminum element, nickel element and molybdenum element.
- 3. (Currently Amended) The metal laminate according to claim 1, wherein the insulating layer is a resin selected from the group <del>comprising</del> consisting of polyimide, polyamide, polyamideimide.

- 4. (Currently Amended) The metal laminate according to claim 1, wherein a constitution of the metal laminate is a double-sided metal laminate comprising a metal layer/a polyimide layer/a SUS layer SUS layer/a polyimide layer/a metal layer selected from the group consisting of copper, SUS and copper alloy.
- 5. (Currently Amended) The metal laminate according to claim 4, wherein the polyimide layer comprises a constitution of thermoplastic polyimide layer/non-thermoplastic polyimide layer/thermoplastic polyimide layer.
- 6. (Currently Amended) A flexure which is used in for a suspension for a hard disc, manufactured from a metal laminate according to any one of claims 1 to 5 claim 5.

## 7. (Canceled)

- 8. (Currently Amended) A plasma etching method <u>comprising etching</u> which uses a metal laminate according to <u>claim 5</u> any one of claims 1 to 5 as a material to be etched.
- 9. (Currently Amended) A wet etching method <u>comprising etching</u> of a metal laminate according to any one of claims 1 to 5, where a metal laminate is etched <u>claim 5</u> with alkaline aqueous solution.
- 10. (New) A flexure for a suspension for a hard disc, manufactured from a metal laminate according to claim 4.

- 11. (New) A flexure for a suspension for a hard disc, manufactured from a metal laminate according to claim 3.
- 12. (New) A flexure for a suspension for a hard disc, manufactured from a metal laminate according to claim 2.
- 13. (New) A flexure for a suspension for a hard disc, manufactured from a metal laminate according to claim 1.
- 14. (New) A plasma etching method comprising etching a metal laminate according to claim 4.
- 15. (New) A plasma etching method comprising etching a metal laminate according to claim 3.
- 16. (New) A plasma etching method comprising etching a metal laminate according to claim 2.
- 17. (New) A plasma etching method comprising etching a metal laminate according to claim 1.
- 18. (New) A wet etching method comprising etching a metal laminate according to claim 4 with alkaline aqueous solution.
- 19. (New) A wet etching method comprising etching a metal laminate according to claim 3 with alkaline aqueous solution.

- 20. (New) A wet etching method comprising etching a metal laminate according to claim 2 with alkaline aqueous solution.
- 21. (New) A wet etching method comprising etching a metal laminate according to claim 1 with alkaline aqueous solution.
- 22. (New) A method for manufacturing a metal laminate comprising laminating a metal layer to an insulating layer where the insulating layer is to be subjected to an etching processing, wherein the metal layer is selected so that the surface of the metal layer which is in contact with the insulating layer, has a thickness of a metal oxide film of the surface of the metal layer measured at a time when atomic concentrations of the main metal element and the oxygen element constituting the metal layer are equal to each other in a range of at least 0Å to less than 50Å, the respective concentrations of main metal element and oxygen element constituting the metal layer being measured from the surface of the metal layer towards the inside of the metal layer in a time-elapsing manner according to AES (Auger electron spectroscopy).